

P54/74FCT861AT/BT/CT—P54/74FCT863AT/BT/CT P54/74FCT864AT/BT/CT BUS INTERFACE TRANSCEIVERS



FEATURES

- Function, Pinout and Drive Compatible with the FCT, F Logic and AM29861/863/864
- FCT-C speed at 5.1ns max. (Com'I)
FCT-B speed at 6.0ns max. (Com'I)
- Reduced V_{OH} (typically = 3.3V) versions of Equivalent FCT functions
- Edge-rate Control Circuitry for Significantly Improved Noise Characteristics
- ESD protection exceeds 2000V
- Power-off disable feature
- Matched Rise and Fall times
- Fully Compatible with TTL Input and Output Logic Levels
- 64 mA Sink Current (Com'I), 32 mA (Mil)
15 mA Source Current (Com'I), 12 mA (Mil)
- Buffered Common Clear and Preset Input
- High Speed Parallel Latches
- Buffered Common Latch Enable Input
- Manufactured in 0.7 micron PACE Technology™



DESCRIPTION

The 'FCT860T bus interface transceivers provide high-performance interface buffering for wide data/address paths or buses carrying parity. The 'FCT861T is a non-inverting, 10-bit transceiver. The 'FCT863T and 'FCT864T are 9-bit transceivers having NAND-ed output enables for maximum control flexibility. The 'FCT864T is the inverting version of the 'FCT863T.

The 'FCT800T high performance interface family is designed for high-capacitance load drive capability while providing low-capacitance bus loading at both inputs and outputs. All inputs have clamp diodes and all outputs are

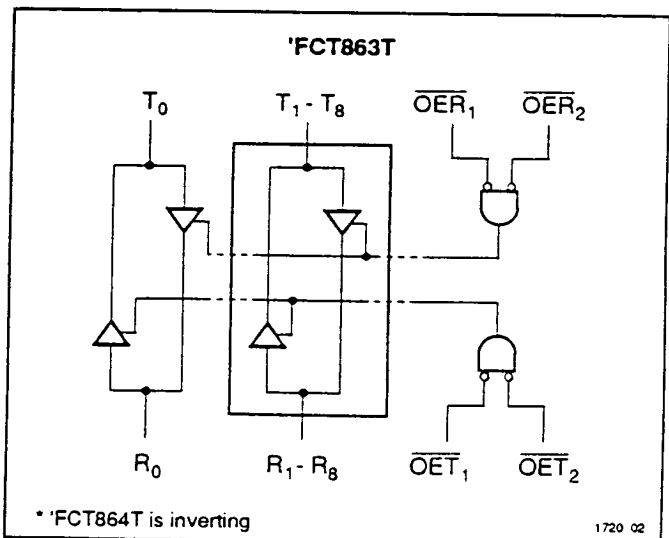
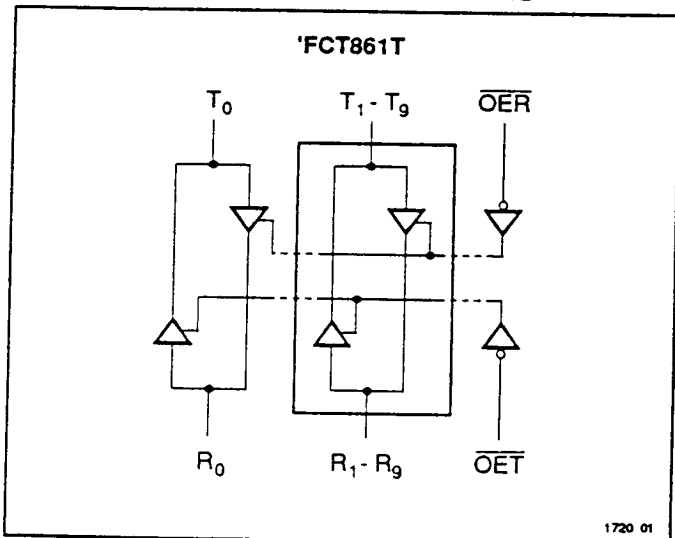
designed for low-capacitance bus loading in the high impedance state.

The 'FCT800T interface family are manufactured using PACE Technology™ which is Performance Advanced CMOS Engineered to use 0.7 micron effective channel lengths giving 400 picosecond loaded* internal gate delays. PACE Technology includes two-level metal and epitaxial substrates. In addition to very high performance and very high density, the technology features latch-up protection, single event upset protection, and is supported by a Class 1 environment volume production facility.

* For a fan-in/fan-out of 4, at 85°C junction temperature and 5.0V.



FUNCTIONAL BLOCK DIAGRAMS



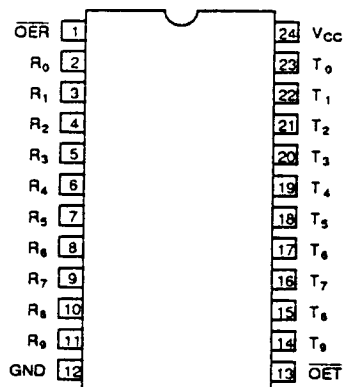
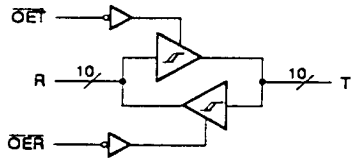
Means Quality, Service and Speed

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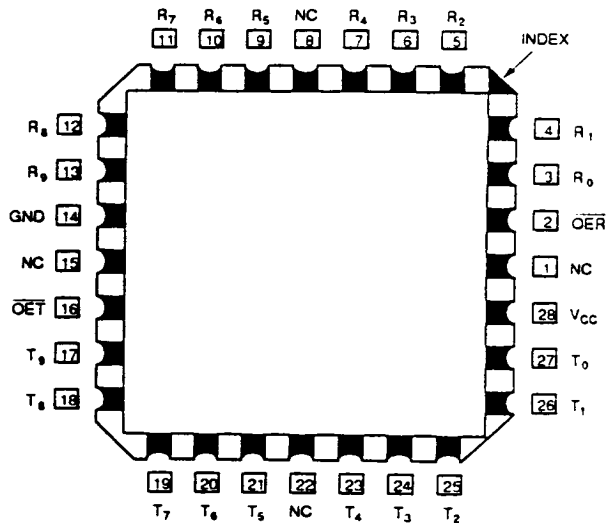
LOGIC SYMBOLS

PIN CONFIGURATIONS

'FCT861T 10-BIT TRANSCEIVER



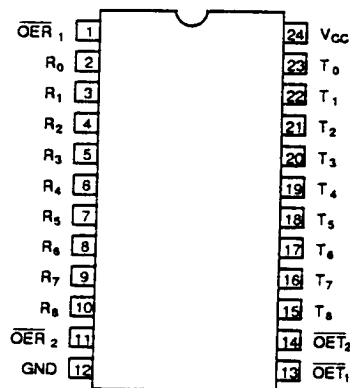
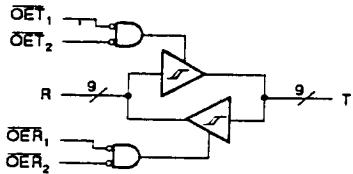
DIP (D4, P4), SOIC (S4)



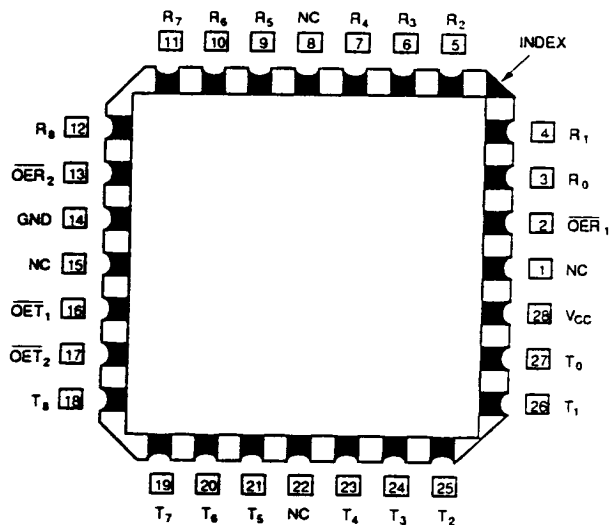
LCC (L5-1)

1720 03

'FCT863T/864T 9-BIT TRANSCEIVER



DIP (D4, P4), SOIC (S4)



LCC (L5-1)

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* 'FCT864T is inverting

PIN DESCRIPTION

Name	I/O	Description
'FCT861T		
\overline{OER}	I	When LOW in conjunction with \overline{OET} HIGH activates the RECEIVE mode.
\overline{OET}	I	When LOW in conjunction with \overline{OER} HIGH activates the TRANSMIT mode.
R_i	I/O	10-bit RECEIVE input/output.
T_i	I/O	10-bit TRANSMIT input/output.
'FCT863T/864T		
\overline{OER}_i	I	When LOW in conjunction with \overline{OET}_i HIGH activates the RECEIVE mode.
\overline{OET}_i	I	When LOW in conjunction with \overline{OER}_i HIGH activates the TRANSMIT mode.
R_i	I/O	9-bit RECEIVE input/output.
T_i	I/O	9-bit TRANSMIT input/output.

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TRUTH TABLE¹

'FCT861T/863T (Non-inverting)

Inputs				Outputs		Function
\overline{OET}	\overline{OER}	R_i	T_i	R_i	T_i	
L	H	L	N/A	N/A	L	Transmitting
L	H	H	N/A	N/A	H	Transmitting
H	L	N/A	L	L	N/A	Receiving
H	L	N/A	H	H	N/A	Receiving
H	H	X	X	Z	Z	High-Z

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NOTE:

1. H = HIGH, L = LOW, Z = Impedance, X = Don't Care, N/A = Not Applicable.

ABSOLUTE MAXIMUM RATINGS^{1,2}

Symbol	Parameter	Value	Unit
T _{STG}	Storage Temperature	-65 to +150	°C
T _A	Ambient Temperature Under Bias	-65 to +135	°C
V _{CC}	V _{CC} Potential to Ground	-0.5 to +7.0	V
P _T	Power Dissipation	0.5	W

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Symbol	Parameter	Value	Unit
I _{OUTPUT}	Current Applied to Output	120	mA
V _{IN}	Input Voltage	-0.5 to +7.0	V
V _{OUT}	Voltage Applied to Output	-0.5 to +7.0	V

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- Notes:**
- Operation beyond the limits set forth in the above table may impair the useful life of the device. Unless otherwise noted, these limits are over the operating free-air temperature range.
 - Unused inputs must always be connected to an appropriate logic voltage level, preferably either V_{CC} or ground.

RECOMMENDED OPERATING CONDITIONS

Free Air Ambient Temperature	Min	Max
Military	-55°C	+125°C
Commercial	0°C	+70°C

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Supply Voltage (V _{CC})	Min	Max
Military	+3.1V	+3.5V
Commercial	+3.1V	+3.5V

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DC ELECTRICAL CHARACTERISTICS (Over recommended operating conditions)

Symbol	Parameter	Min	Typ ¹	Max	Units	V _{CC}	Conditions	
V _{IH}	Input HIGH Voltage	2.0			V			
V _{IL}	Input LOW Voltage			0.8	V			
V _H	Hysteresis		0.35		V		All inputs	
V _{IK}	Input Clamp Diode Voltage		-0.7	-1.2	V	MIN	I _{IN} = -18mA	
V _{OH}	Output HIGH Voltage	Military	2.4	3.3	V	MIN	I _{OH} = -12mA I _{OH} = -15mA	
		Commercial	2.4	3.3	V	MIN		
V _{OL}	Output LOW Voltage	Military		0.3	0.5	V	MIN	I _{OL} = 32mA I _{OL} = 48mA I _{OL} = 64mA
		Commercial		0.3	0.5	V	MIN	
		Commercial		0.3	0.5	V	MIN	
I _I	Input HIGH Current			20	μA	MAX	V _{IN} = V _{CC}	
I _{IH}	Input HIGH Current			5	μA	MAX	V _{IN} = 2.7V	
I _{IL}	Input LOW Current			-5	μA	MAX	V _{IN} = 0.5V	
I _{OZH}	Off State I _{OUT} HIGH-Level Output Current			10	μA	MAX	V _{OUT} = 2.7V	
I _{OZL}	Off State I _{OUT} LOW-Level Output Current			-10	μA	MAX	V _{OUT} = 0.5V	
I _{OS}	Output Short Circuit Current ²	-60	-120	-225	mA	MAX	V _{OUT} = 0.0V	
I _{OFF}	Power-off Disable			100	μA	0V	V _{OUT} = 4.5V	
C _{IN}	Input Capacitance ³		5	10	pF	MAX	All inputs	
C _{OUT}	Output Capacitance ³		9	12	pF	MAX	All outputs	
I _{CC}	Quiescent Power Supply Current		0.2	1.5	mA	MAX	V _{IN} < 0.2V, V _{IN} ≥ V _{CC} - 0.2V	

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- Notes:**
- Typical limits are at V_{CC} = 3.3V, T_A = +25°C ambient.
 - Not more than one output should be shorted at a time. Duration of short should not exceed one second. The use of high speed test apparatus and/or sample and hold techniques are preferable in order to minimize internal chip heating and more accurately reflect

- operational values. Otherwise prolonged shorting of a high output may raise the chip temperature well above normal and thereby cause invalid readings in other parameter tests. In any sequence of parameter tests, I_{OS} tests should be performed last.
- This parameter is guaranteed but not tested.

DC CHARACTERISTICS (Over recommended operating conditions unless otherwise specified.)

Symbol	Parameter	Typ ¹	Max	Units	Conditions
ΔI_{CC}	Quiescent Power Supply Current (TTL inputs)	0.2	2.0	mA	$V_{CC} = \text{MAX}$, $V_{IN} = 2.7V^2$, $f_1 = 0$, Outputs Open
I_{CCD}	Dynamic Power Supply Current ³	0.15	0.25	mA/ mHz	$V_{CC} = \text{MAX}$, One Input Toggling, 50% Duty Cycle, Outputs Open, \overline{OER} or $\overline{OET} = \text{GND}$, $V_{IN} \leq 0.2V$ or $V_{IN} \geq V_{CC} - 0.2V$
I_C	Total Power Supply Current ⁵	1.7	4.0	mA	$V_{CC} = \text{MAX}$, 50% Duty Cycle, Outputs Open, One Bit Toggling at $f_1 = 10\text{MHz}$, \overline{OER} or $\overline{OET} = \text{GND}$, $V_{IN} \leq 0.2V$ or $V_{IN} \geq V_{CC} - 0.2V$
		2.0	5.0	mA	$V_{CC} = \text{MAX}$, 50% Duty Cycle, Outputs Open, One Bit Toggling at $f_1 = 10\text{MHz}$, \overline{OER} or $\overline{OET} = \text{GND}$, $V_{IN} = 2.7V$ or $V_{IN} = \text{GND}$
		3.2	6.5 ⁴	mA	$V_{CC} = \text{MAX}$, 50% Duty Cycle, Outputs Open, Eight Bits Toggling at $f_1 = 2.5\text{MHz}$, \overline{OER} or $\overline{OET} = \text{GND}$, $V_{IN} \leq 0.2V$ or $V_{IN} \geq V_{CC} - 0.2V$
		5.2	14.5 ⁴	mA	$V_{CC} = \text{MAX}$, 50% Duty Cycle, Outputs Open, Eight Bits Toggling at $f_1 = 2.5\text{MHz}$, \overline{OER} or $\overline{OET} = \text{GND}$, $V_{IN} = 2.7V$ or $V_{IN} = \text{GND}$

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Notes:

- Typical values are at $V_{CC} = 3.3V$, $+25^\circ\text{C}$ ambient.
- Per TTL driven input ($V_{IN} = 2.7V$); all other inputs at V_{CC} or GND.
- This parameter is not directly testable, but is derived for use in Total Power Supply calculations.
- Values for these conditions are examples of the I_{CC} formula. These limits are guaranteed but not tested.
- $$I_C = I_{\text{QUIESCENT}} + I_{\text{INPUTS}} + I_{\text{DYNAMIC}}$$

$$I_C = I_{CC} + \Delta I_{CC} D_H N_T + I_{CCD} (f_0/2 + f_1 N_1)$$

$$I_{CC} = \text{Quiescent Current with CMOS input levels}$$

ΔI_{CC} = Power Supply Current for a TTL High Input ($V_{IN} = 2.7V$)

D_H = Duty Cycle for TTL Inputs High

N_T = Number of TTL Inputs at D_H

I_{CCD} = Dynamic Current Caused by an Input Transition Pair (HLH or LHL)

f_0 = Clock Frequency for Register Devices (Zero for Non-Register Devices)

f_1 = Input Frequency

N_1 = Number of Inputs at f_1

All currents are in milliamps and all frequencies are in megahertz.

SWITCHING CHARACTERISTICS OVER OPERATING RANGE

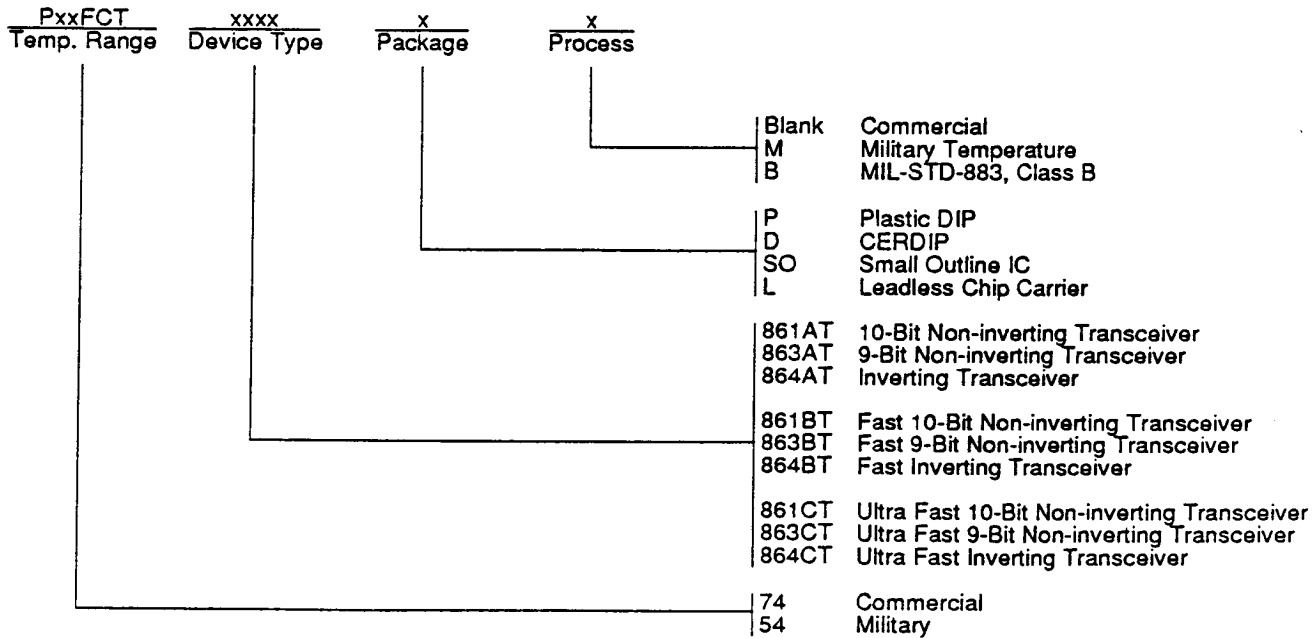
Sym.	Parameter	Test Conditions ¹	FCT861AT/863AT/864AT		FCT861BT/863BT/864BT		FCT861CT/863CT/864CT				Units				
			MIL		COM'L		MIL		COM'L			MIL		COM'L	
			Min. ²	Max.	Min. ²	Max.	Min. ²	Max.	Min. ²	Max.		Min. ²	Max.	Min. ²	Max.
t _{PLH} t _{PHL}	Propagation Delay R _i to T _i or T _i to R _i FCT861T/863T	C _L = 50pF R _L = 500Ω	—	9.0	—	8.0	—	6.5	—	6.0	2.0	5.6	2.0	5.1	ns
		C _L = 300pF ³ R _L = 500Ω	—	17.0	—	15.0	—	14.0	—	13.0	4.0	13.0	4.0	12.0	ns
t _{PLH} t _{PHL}	Propagation Delay R _i to T _i or T _i to R _i FCT864T	C _L = 50pF R _L = 500Ω	—	9.0	—	7.5	—	6.5	—	5.5	2.0	5.3	2.0	4.7	ns
		C _L = 300pF ³ R _L = 500Ω	—	16.0	—	14.0	—	14.0	—	13.0	4.0	12.5	4.0	11.5	ns
t _{PZH} t _{PZL}	Output Enable Time OET to T _i or OER to R _i	C _L = 50pF R _L = 500Ω	—	13.0	—	12.0	—	9.0	—	8.0	2.0	7.6	2.0	6.8	ns
		C _L = 300pF ³ R _L = 500Ω	—	22.0	—	20.0	—	16.0	—	15.0	4.0	15.0	4.0	14.0	ns
t _{PHZ} t _{PLZ}	Output Disable Time OET to T _i or OER to R _i	C _L = 5pF ³ R _L = 500Ω	—	9.0	—	9.0	—	7.0	—	6.0	1.5	6.1	1.5	5.1	ns
		C _L = 50pF R _L = 500Ω	—	10.0	—	10.0	—	8.0	—	7.0	2.0	6.6	2.0	5.6	ns

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Notes:

1. See test circuit and waveforms.
2. Minimum limits are guaranteed but not tested on Propagation Delays.
3. This parameters are guaranteed but not tested.

ORDERING INFORMATION



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